

Title (en)

Material for a semiconductor device carrier substrate and method of producing the same

Title (de)

Material für Halbleiter-Trägersubstrat und seine Herstellung

Title (fr)

Matériau pour substrat supportant des semi-conducteurs et fabrication associée

Publication

EP 0813243 A2 19971217 (EN)

Application

EP 97109681 A 19970613

Priority

- JP 17573096 A 19960614
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- JP 13616497 A 19970509

Abstract (en)

To provide a substrate material made of an aluminum/silicon carbide composite alloy which has a thermal conductivity of 100 W/mxK or higher and a thermal expansion coefficient of 20×10^{-6} / DEG C or lower and is lightweight and compositionally homogeneous. A substrate material made of an aluminum/silicon carbide composite ally which comprises Al-SiC alloy composition parts and non alloy composition part and dispersed therein from 10 to 70% by weight silicon carbide particles, and in which the fluctuations of silicon carbide concentration in the Al-SiC alloy composition parts therein are within 1% by weight. The substrate material is produced by sintering a compact of an aluminum/silicon carbide starting powder at a temperature not lower than 600 DEG C in a non-oxidizing atmosphere. <IMAGE>

IPC 1-7

H01L 23/15

IPC 8 full level

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CPC (source: EP US)

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